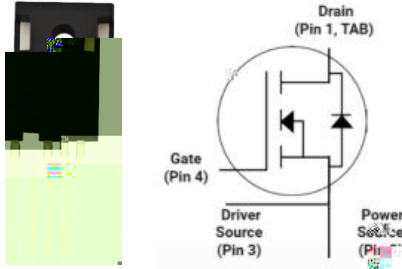


SG2M035120UJ

TriQSiC™ 1200V Silicon Carbide Power MOSFET G2

Features

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Benefits

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-
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Applications

-
-
-
-

Table 1 Key performance and package parameters

Type	V_{DS}	I_{DS}	$R_{DS(on), typ}$	$T_{J,max}$	Marking	Package

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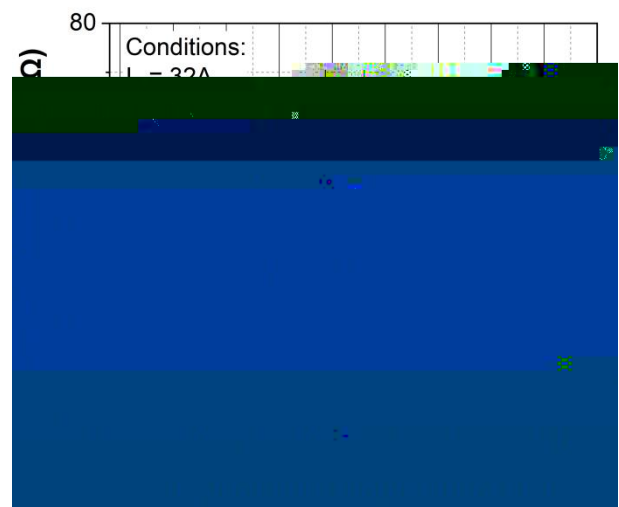
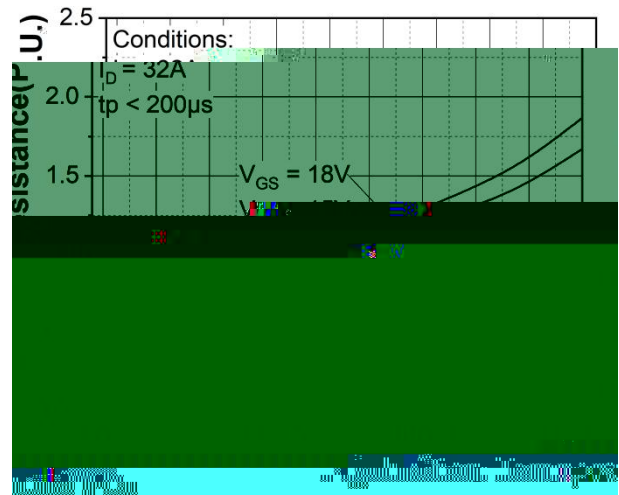
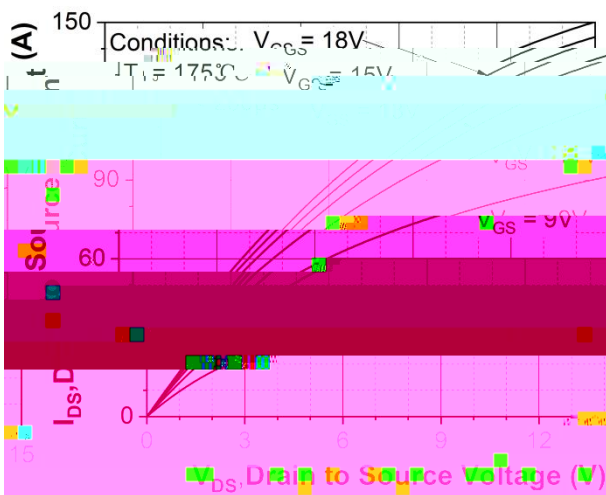
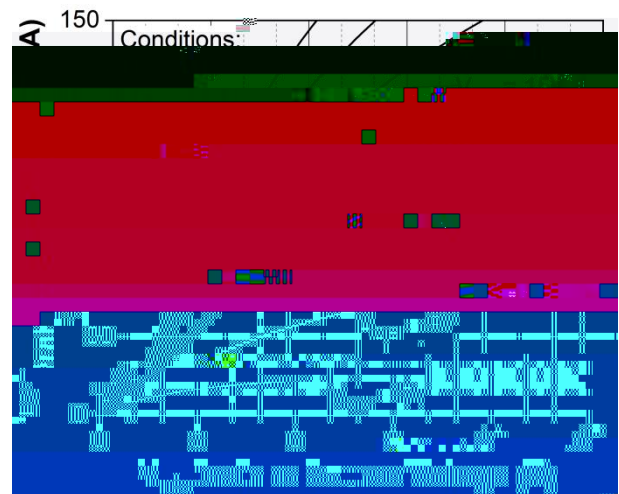
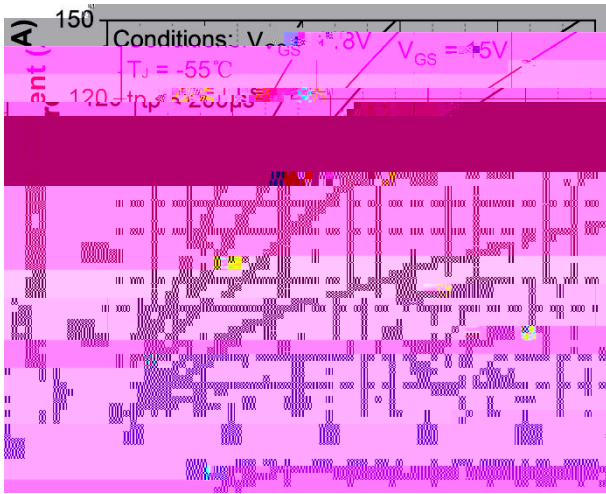
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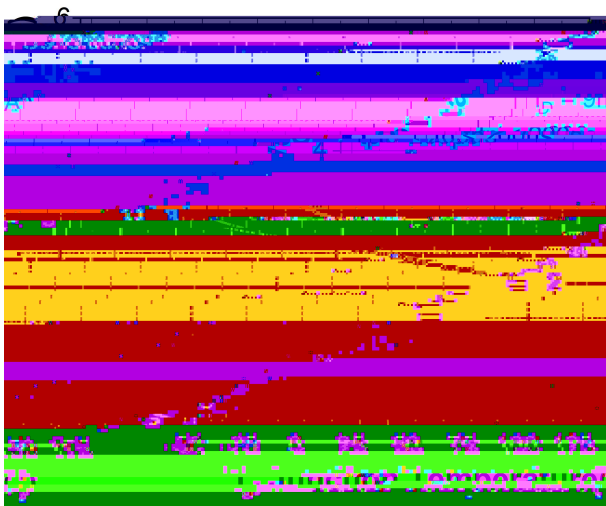
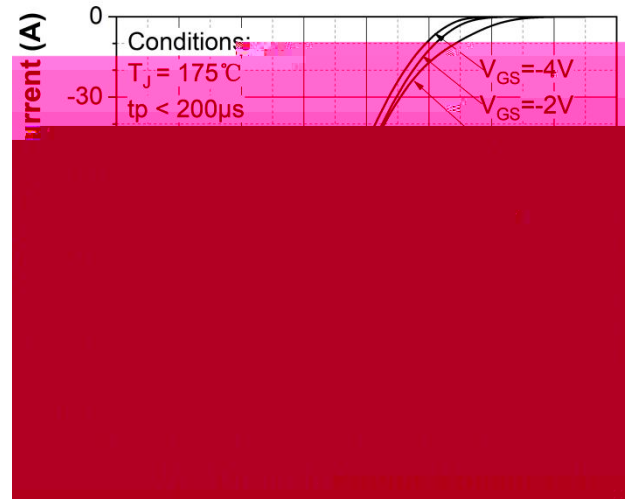
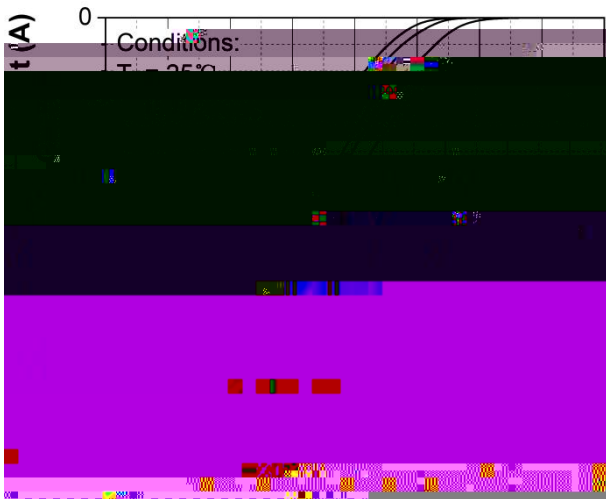
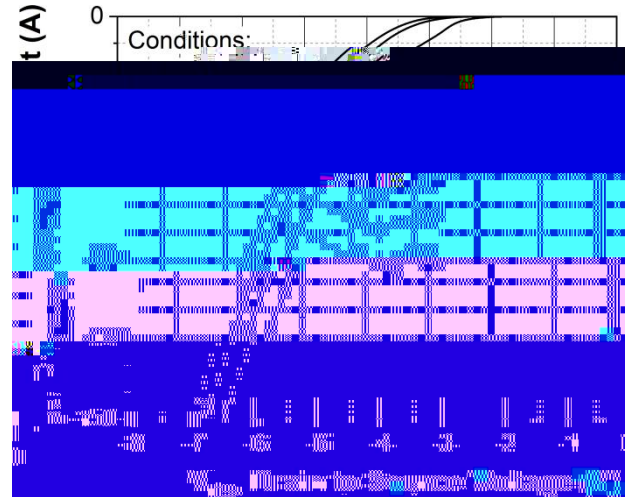
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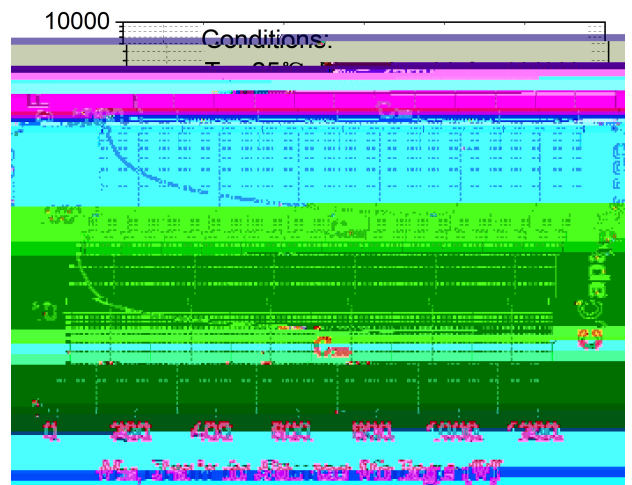
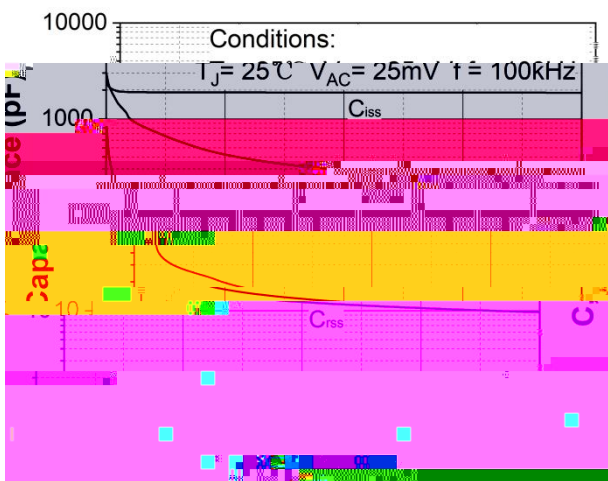
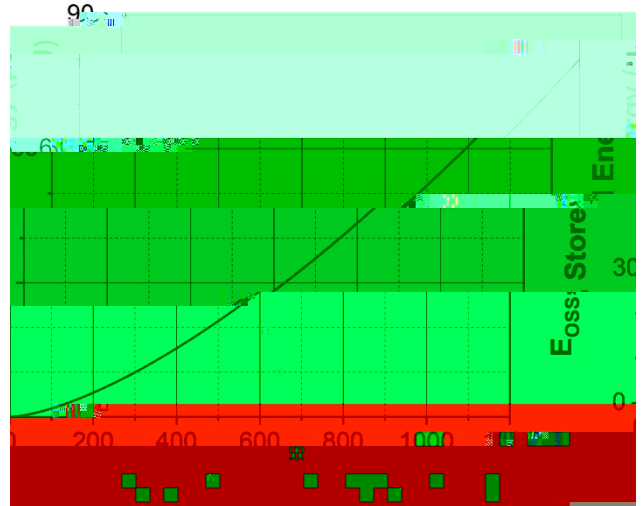
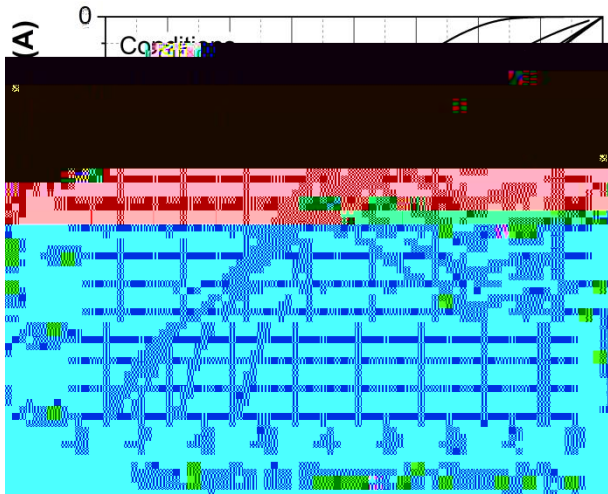
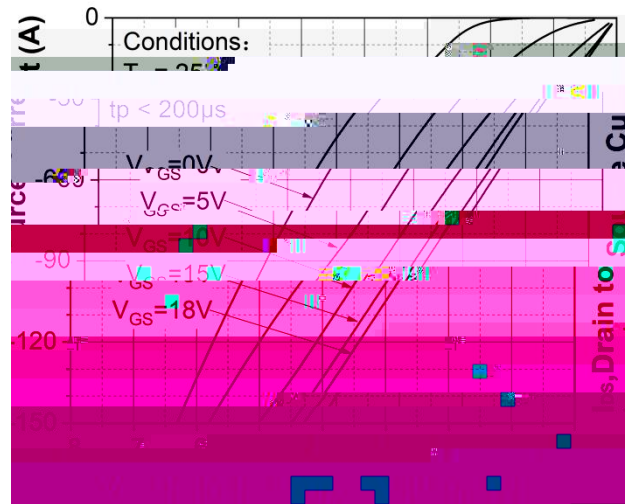
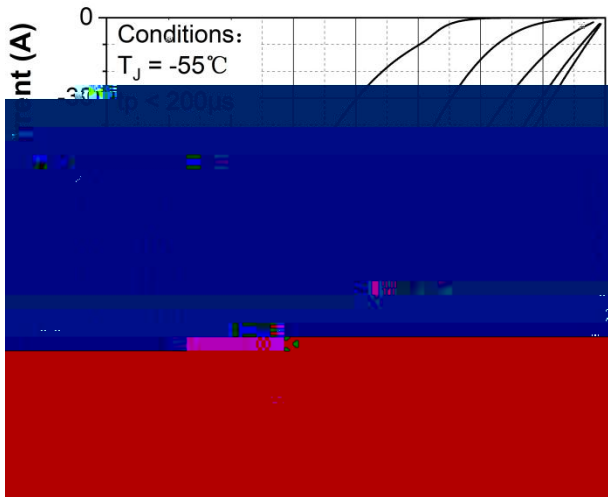
4 Electrical characteristic diagrams



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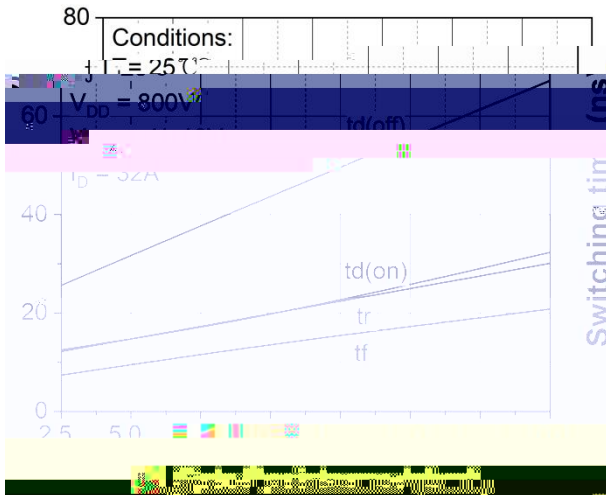
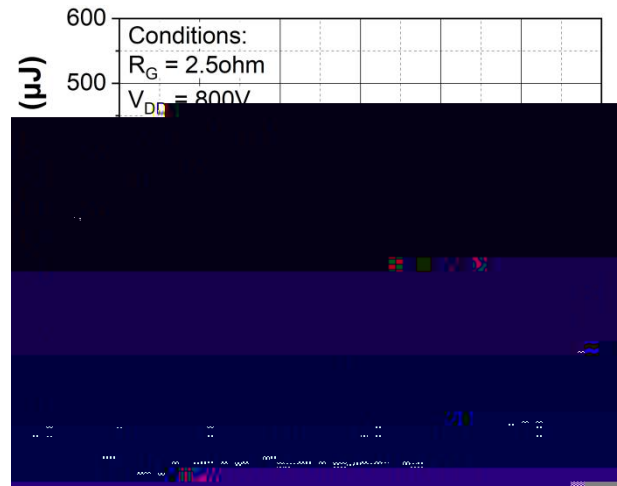
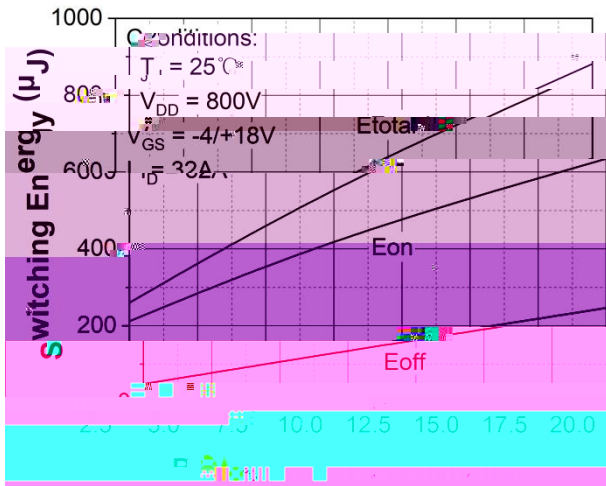
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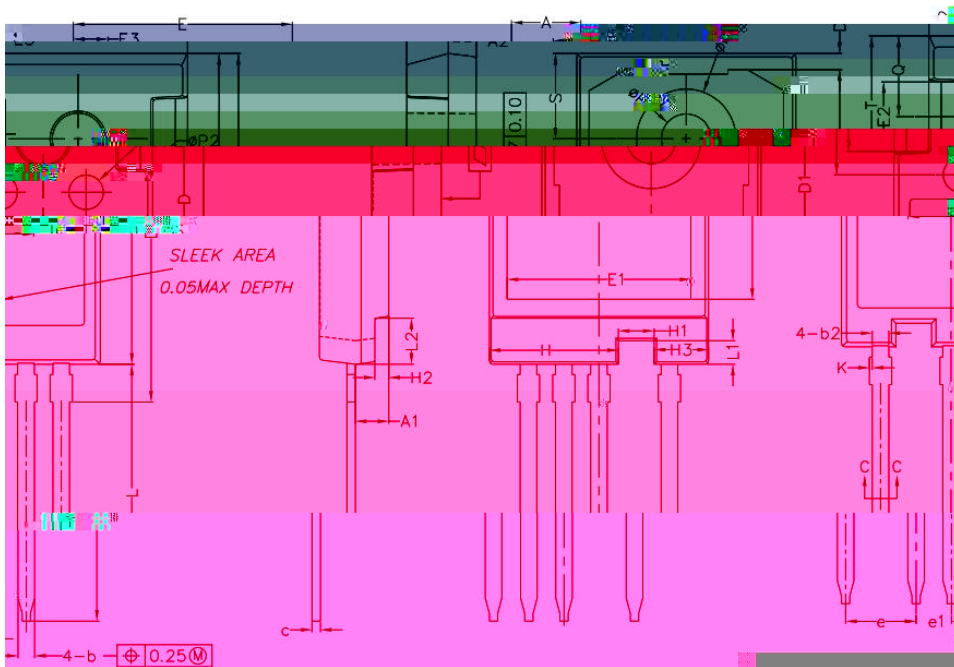


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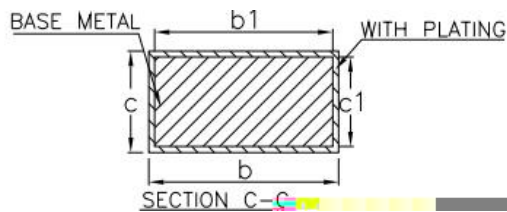
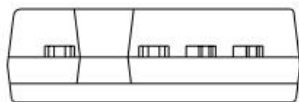
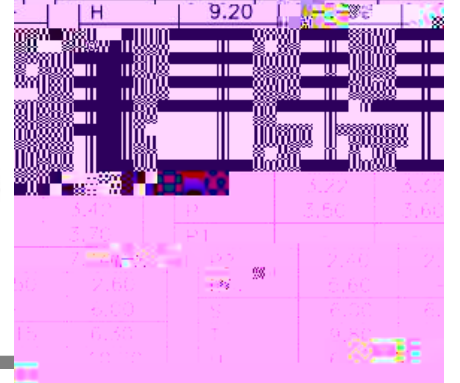
1200V SiC Power MOSFET

5 Package drawing



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	MAX	MAX
A	4.90	5.00	5.10
A1	2.51	2.41	2.51
A2	1.90	2.00	2.10
b	1.16	-	1.29
b1	1.15	1.29	1.25
b2	1.16	-	1.29
c	0.58	-	0.66
c1	0.58	0.60	0.62
D	22.30	22.40	22.50
D1	16.25	16.55	16.85
D2	1.05	1.20	1.35
D3	24.97	25.12	25.27
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	4.98	5.08	5.18
e1	2.44	2.54	2.64

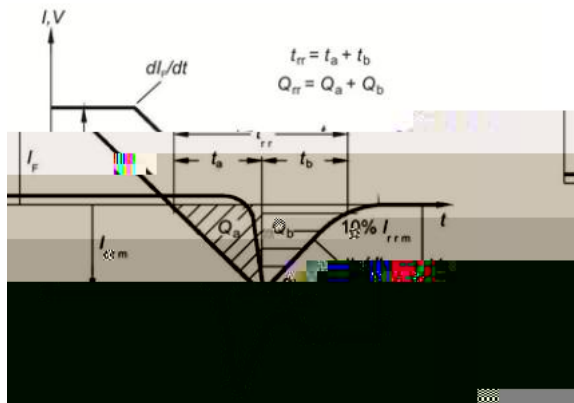
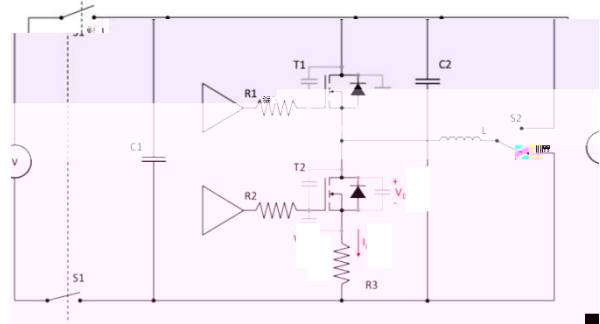
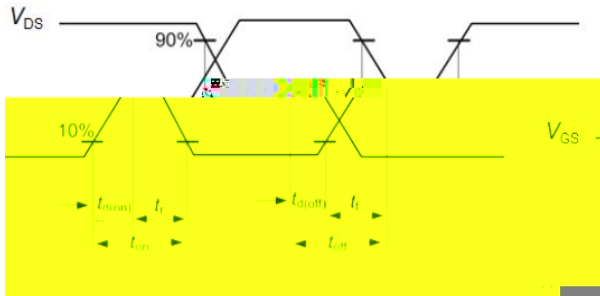


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6 Test conditions



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1200V SiC Power MOSFET

Revision history

Document versio

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